

Title (en)  
SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

Title (de)  
HALBLEITERBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)  
DISPOSITIF SEMI-CONDUCTEUR ET PROCEDE DE FABRICATION CORRESPONDANT

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Application  
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Abstract (en)  
The main object of the present invention is to provide a semiconductor device (LSI chip) in which chippings (chippings at cut surface edges) do not occur or are reduced to an practically allowable level even if they occur at the time of separating LSI chips from a wafer by dicing and a method for fabricating the same. <??>In order to achieve the above object, a semiconductor device of the invention is characterized in that at least edge portions of a surface on which a device is formed of a semiconductor chip and a back surface thereof are chamfered to have a slant surface having a chamfering slant angle  $\theta$ , respectively, where  $90 \text{ DEG} < \theta < 180 \text{ DEG}$ . <??>A more preferable chamfering slant angle  $\theta$  is not less than  $100 \text{ DEG}$  and not more than  $135 \text{ DEG}$  and further it is the most practically preferable that all of the chamfering slant angles of four sides of the semiconductor chip are about  $135 \text{ DEG}$ . <??>According to this invention, it is possible to prevent the outer peripheral edge portions of the LSI chips from being chipped at the time of separating the LSI chips from the wafer by dicing. Hence, if this chip is mounted on an IC card or an IC tag, it is possible to reduce material cost and fabrication time by a simple structure and, in particular, to realize a low-profile IC card that is as highly reliable even without a reinforcing board as in a state with the reinforcing board in the mounting of the LSI chip on the IC card, and an IC tag that has high yield and high reliability in the mounting of the LSI on the IC tag, respectively. <IMAGE>

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IPC 8 full level  
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